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October 2013

FQP9P25

P-Channel QFET® MOSFET -250 V, -9.4 A, 620 mΩ

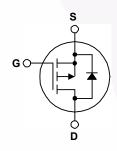
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -9.4 A, -250 V, $R_{DS(on)}$ = 0.62 Ω (Max.)@ V_{GS} = -10 V, I_D = -4.7 A
- Low gate charge (typ. 29 nC)
- Low Crss (typ. 27 pF)
- · 100% avalanche tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

3 °				
Symbol	Parameter		FQP9P25	Unit
V_{DSS}	Drain-Source Voltage		-250	V
I _D	Drain Current - Continuous (T _C = 25°	C)	-9.4	Α
	- Continuous (T _C = 100	0°C)	-5.9	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	-37.6	Α
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	650	mJ
I _{AR}	Avalanche Current	(Note 1)	-9.4	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.5	V/ns
P_{D}	Power Dissipation (T _C = 25°C)		120	W
	- Derate above 25°C		0.96	W/°C
T _J , T _{STG}	Operating and Storage Temperature Rar	nge	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQP9P25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.04	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQP9P25	FQP9P25	TO220	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-250			٧
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-0.2		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -250 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = -200 \text{ V}, T_{C} = 125^{\circ}\text{C}$			-1 -10	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 30 V, V _{DS} = 0 V			100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, I_D = -4.7 \text{ A}$		0.48	0.62	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = -40 \text{ V}, I_{D} = -4.7 \text{ A}$		5.7		S

Dynamic Characteristics

C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$	 910	1180	pF
Coss	Output Capacitance	f = 1.0 MHz	 170	220	pF
C _{rss}	Reverse Transfer Capacitance		 27	35	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	V _{DD} = -125 V, I _D = -9.4 A,		20	50	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		150	310	ns
t _{d(off)}	Turn-Off Delay Time	G -		45	100	ns
t _f	Turn-Off Fall Time	(Note 4)		65	140	ns
Q_g	Total Gate Charge	$V_{DS} = -200 \text{ V}, I_{D} = -9.4 \text{ A},$		29	38	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V	/	7.6		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		14		nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		 	-9.4	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		 	-37.6	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -9.4 A	 	-5.0	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{S} = -9.4 \text{ A},$	 190		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs	 1.45		μС

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 11.8mH, I_{AG} = -9.4A, V_{DD} = -50V, R_{G} = 25 Ω , Starting T_{J} = 25°C 3. I_{SD} ≤ -9.4A, di/dt ≤ 300A/µs, V_{DD} ≤ BVDSS, Starting T_{J} = 25°C 4. Essentially independent of operating temperature

Typical Characteristics

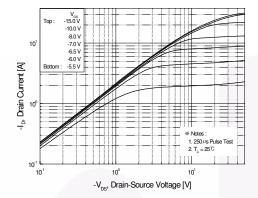


Figure 1. On-Region Characteristics

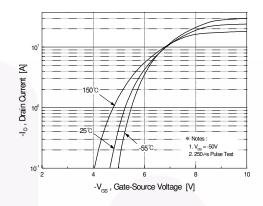


Figure 2. Transfer Characteristics

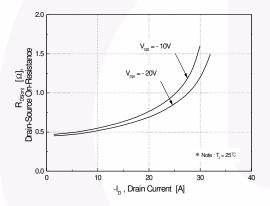


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

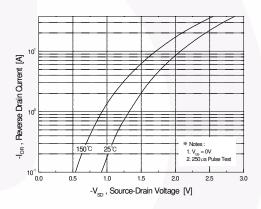


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

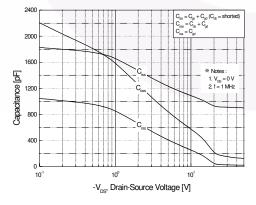


Figure 5. Capacitance Characteristics

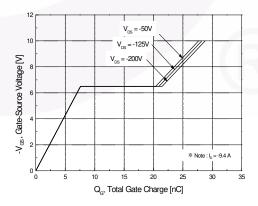


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

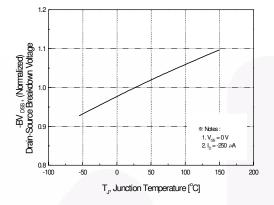


Figure 7. Breakdown Voltage Variation vs. Temperature

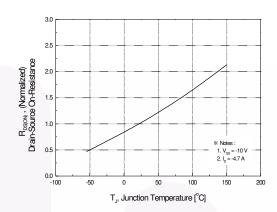


Figure 8. On-Resistance Variation vs. Temperature

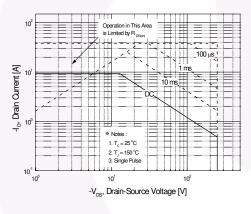


Figure 9. Maximum Safe Operating Area

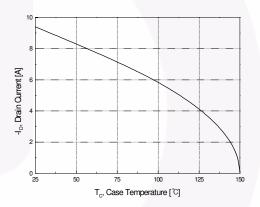


Figure 10. Maximum Drain Current vs. Case Temperature

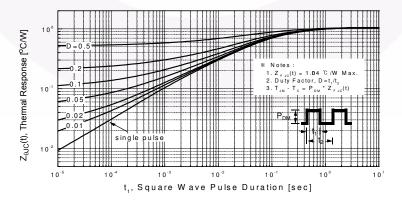


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

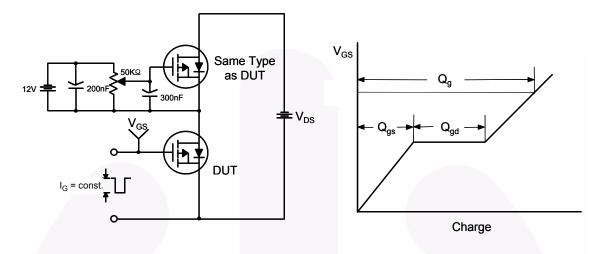


Figure 13. Resistive Switching Test Circuit & Waveforms

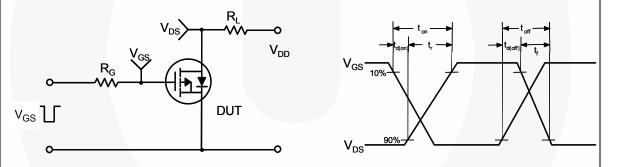


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

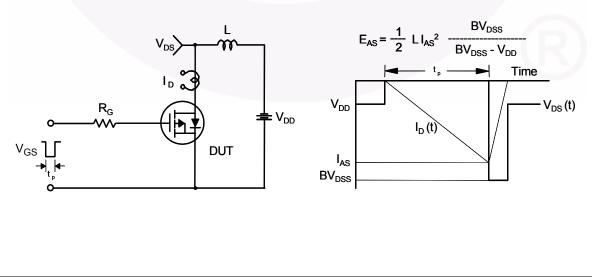


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms DUT I_{SD} o Driver Compliment of DUT ‡ VDD (N-Channel) $\prod V_{GS}$ • dv/dt controlled by R_G \bullet I_{SD} controlled by pulse period Gate Pulse Width V_{GS} Gate Pulse Period 10V (Driver) **Body Diode Reverse Current** I_{SD} (DUT) di/dt I_{FM} , Body Diode Forward Current V_{DS} V_{SD} (DUT) Body Diode Forward Voltage Drop Body Diode Recovery dv/dt

Mechanical Dimensions

TO-220 3L

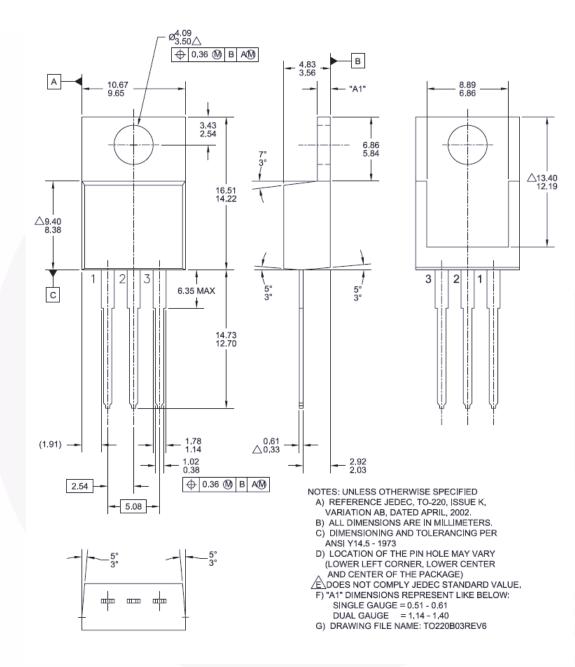


Figure 16. TO-220, Molded, 3Lead, Jedec Variation AB

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Dimension in Millimeters





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